

isc Silicon NPN Power Transistor

2SC2507

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V(\text{Min})$
- Fast Switching Speed
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 0.7V(\text{Max.}) @ I_C = 10A$

APPLICATIONS

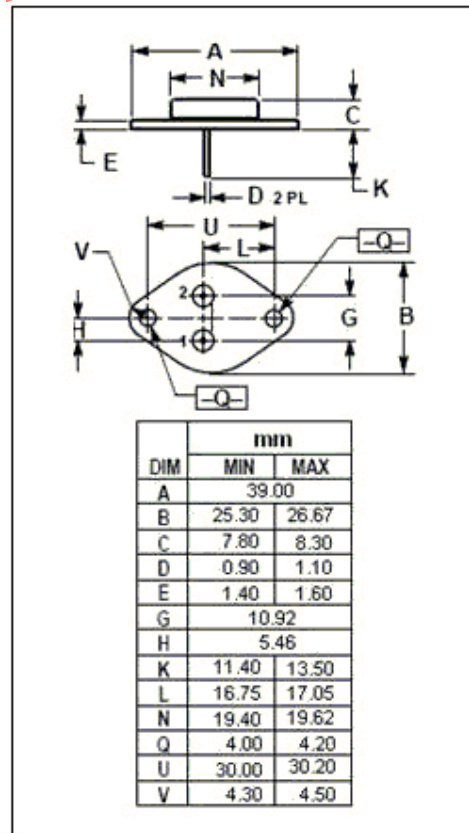
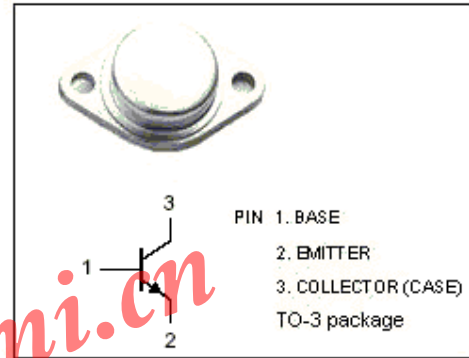
- Designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220V switchmode applications such as switching regulator's, inverters.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	20	A
I_{CM}	Collector Current-Peak	40	A
I_B	Base Current-Continuous	7	A
I_{BM}	Base Current-Peak	14	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	200	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.625	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.2\text{A}; I_B=0$	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=1\text{A}$			0.7	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=1\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=500\text{V}; I_E=0$			100	μA
I_{CEO}	Collector Cutoff Current	$V_{CE}=320\text{V}; I_B=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			1.0	mA
h_{FE-1}	DC Current Gain	$I_C=10\text{A}; V_{CE}=2\text{V}$	15			
h_{FE-2}	DC Current Gain	$I_C=20\text{A}; V_{CE}=2\text{V}$	8			
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=10\text{V}$		20		MHz

Switching times

t_{on}	Turn-on Time	$I_C=10\text{A}; I_{B1}=-I_{B2}=2\text{A}$ $R_L=3\Omega; V_{BB2}=4\text{V}$			1.0	μs
t_{stg}	Storage Time				3.0	μs
t_f	Fall Time				0.7	μs